imall

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UP04315

Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For switching/digital circuits

Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR2215 + UNR2115

Absolute Maximum Ratings $T_a = 25^{\circ}C$

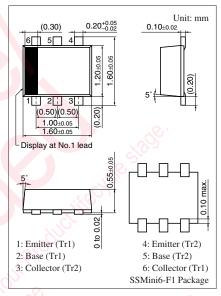
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	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	50	v
	Collector-emitter voltage (Base open)	V _{CEO}	50	V
	Collector current	I _C	100	mA
Tr2	Collector-base voltage (Emitter open)	V _{CBO}	-50	NO NO
	Collector-emitter voltage (Base open)	V _{CEO}	-50	v
	Collector current	I _C	-100	mA
Overall	Total power dissipation	P _T	125	mW
	Junction temperature	Tj	125	<u>∕°C }</u>
	Storage temperature	T _{stg}	-55 to +125	°C



• Tr1

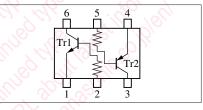
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 6 V, I_C = 0$			0.01	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	160		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{C} = 10 \text{ mA}, I_{B} = 0.3 \text{ mA}$			0.25	V
Output voltage high level	V _{OH}	$V_{CC} = 5 \text{ V}, $	4.9			V
Output voltage low level	V _{OL}	$V_{CC} = 5 \text{ V}, \text{V}_{\text{B}} = 2.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k} \Omega$			0.2	V
Input resistance	R ₁		-30%	10	+30%	kΩ
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



Marking Symbol: CB

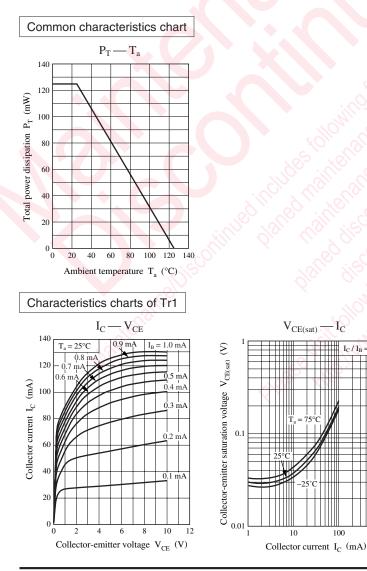
Internal Connection

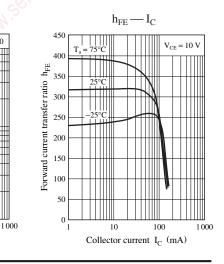


Electrical Characteristics (continued) $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr2						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 V, I_C = 0$			- 0.01	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	160		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high level	V _{OH}	$V_{CC} = -5 \text{ V}, \text{ V}_{B} = -0.5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low level	V _{OL}	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	10	+30%	kΩ
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

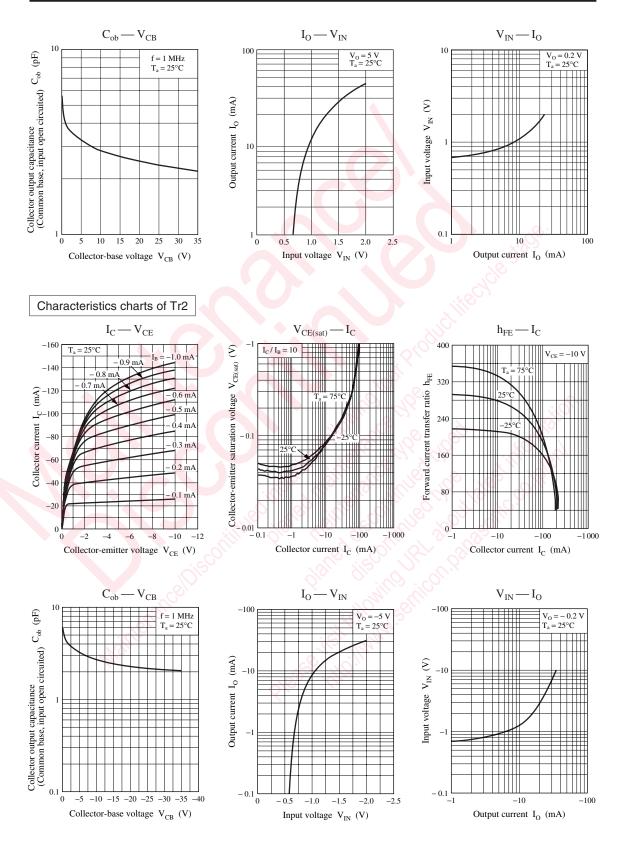




100

 $I_{C} / I_{B} = 10$

Panasonic



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